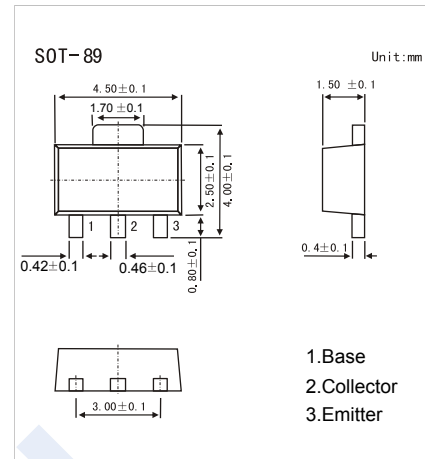


PNP Transistors

2SA1203

■ Features

- Suitable For Output Stage of 3 Watts Amplifier
- Small Flat Package
- $P_c = 1$ to 2W (mounted on ceramic substrate)
- Complementary to 2SC2883



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	-30	V
Collector-Emitter Voltage	V_{CE0}	-30	V
Emitter-Base Voltage	V_{EB0}	-5	V
Collector Current	I_c	-1.5	A
Base Current	I_B	-0.3	A
Collector Power Dissipation	P_c	500	mW
	P_{c^*}	1000	
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature Range	T_{stg}	-55 to +150	$^\circ\text{C}$

* Mounted on ceramic substrate ($250\text{ mm}^2 \times 0.8\text{ t}$)

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_c = -1\text{ mA}, I_E = 0$	-30			V
Collector- emitter breakdown voltage	V_{CE0}	$I_c = -10\text{ mA}, I_B = 0$	-30			
Emitter - base breakdown voltage	V_{EB0}	$I_E = -1\text{ mA}, I_c = 0$	-5			
Collector-base cut-off current	I_{CB0}	$V_{CB} = -30\text{ V}, I_E = 0$			-100	nA
Emitter cut-off current	I_{EB0}	$V_{EB} = -5\text{ V}, I_c = 0$			-100	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = -1.5\text{ A}, I_B = -30\text{ mA}$			-2.0	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_c = -1.5\text{ A}, I_B = -30\text{ mA}$			-1.2	
Base - emitter voltage	V_{BE}	$V_{CE} = -2\text{ V}, I_c = -500\text{ mA}$			-1	
DC current gain	h_{FE}	$V_{CE} = -2\text{ V}, I_c = -500\text{ mA}$	100		320	
Output capacitance	C_{ob}	$V_{CE} = -10\text{ V}, I_E = 0, f = 1\text{ MHz}$			50	pF
Transition frequency	f_T	$V_{CE} = -2\text{ V}, I_E = -500\text{ mA}$		120		MHz

■ Classification of h_{FE}

Type	2SA1203-O	2SA1203-Y
Range	100-200	160-320
Marking	HO	HY

PNP Transistors

2SA1203

■ Typical Characteristics

